

REMARKS

Status of the claims

Claims 1-35 are pending. Claims 1, 4-5, 7, 9 and 15 are amended. Claim 2 and withdrawn claims 31-35 are canceled. Claims 16-30 are allowed. No new matter is added in the claim amendments. Reconsideration of the pending claims is respectfully requested.

Election/Restrictions

Applicants acknowledge the Examiner's rejoining of Groups I and II, claims 1-17 and 18-30, respectively. Applicants have canceled Group III claims 31-35 as being directed to a nonelected invention.

Allowable and allowed subject matter

The Examiner states that claims 2-11 and 15 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form. The Examiner also states that claims 16-30 are allowed. As suggested, Applicants have amended independent claim 1 by incorporating the limitations of allowable dependent claim 2 therein, as discussed *infra*. Claim 2 is canceled. Applicants submit that amended independent claim 1 is allowable. Furthermore, as claims 3-11 and 15 depend directly or indirectly from amended claim 1, they also are allowable.

Title of the invention

The Examiner states the title of the invention is not descriptive of the method that is Applicants' invention. As suggested, Applicants have amended the title as "Method of Reducing an Electrostatic Charge on a Substrate during a PECVD Process".

Applicants' invention as amended

Applicants' invention with respect to amended independent claim 1 now recites a method of reducing an electrostatic charge on a substrate during a PECVD process by introducing a silicon-containing gas into the deposition chamber and igniting it under conditions to deposit an amorphous silicon conductive layer or a microcrystal silicon conductive layer onto the top surface of a susceptor support plate. During the PECVD process, the top conductive layer dissipates the electrostatic charge from the bottom surface of a substrate through the conductive layer. The electrostatic charge on the substrate is reduced thereby during a PECVD process.

Dependent claim 2 is canceled, as discussed. Dependent claims 3-4, 7 and 9 are amended to depend from amended claim 1. Claims 3, 7 and 9 further limit the silicon-containing gas and the pressure and radiofrequency power conditions for deposition of the conductive layer, respectively. Claim 8 depends from dependent claim 7 and further limits the deposition pressure. Claims 10-11 depend from dependent claim 9 and further limit the radiofrequency power.

Claim 4, as amended, and claim 15 depend from claim 1 and further limit the method by introducing an amount of phosphine in hydrogen gas to deposit a

phosphine-doped amorphous or microcrystal silicon conductive layer under. Claims 5-6 depend from dependent claim 4 and limit the phosphine in hydrogen gas mixture.

As claim 1 now incorporates the limitations of introducing a silicon-containing gas to deposit an amorphous or microcrystal silicon conductive layer, Applicants amended dependent claim 15 to recite that the silicon-containing gas is silane. The method further comprises introducing an amount of phosphine in hydrogen gas and igniting both gases under the radiofrequency power and pressure conditions originally recited in the claim. Additionally, claim 15 is amended to recite depositing a phosphine-doped amorphous or microcrystal silicon conductive layer as an active method step.

Claim 12 depends from amended independent claim 1 and limits the substrate to an insulative non-metallic material. Claims 13-14 depend directly and indirectly, respectively, from dependent claim 12 and further limit the insulative non-metallic material.

The 35 U.S.C. §103(a) Rejection

Claims 1 and 12-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over **Tsai et al.** (U.S. Patent No. 6,506,291). Applicants respectfully traverse this rejection.

As discussed *supra*, Applicants have incorporated the limitations of allowable dependent claim 2 into independent claim 1 and canceled claim 2. Thus, amended claim 1 is novel and non-obvious and the rejection as obvious over **Tsai et al.** is moot. Furthermore, claims 12-14 depend directly from amended claim 1 and are, therefore, allowable for depending from an allowable claim, as well as for their respective

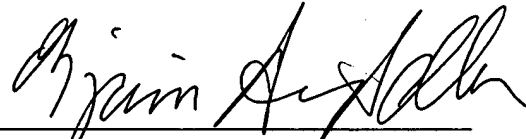
attributes. Accordingly, in view of the claim amendments provided herein, Applicants respectfully request that the rejection of claims 1 and 12-14 under 35 U.S.C. 103(a) be withdrawn.

Applicants submit that claims 1 and 3-30, as presented herein, are in condition for allowance. Accordingly, Applicants request that claims 1 and 3-30 be passed to issuance. This is intended to be a complete response to the Office Action mailed June 18, 2004. If any issues remain, please telephone the undersigned attorney of record for immediate resolution. Applicants believe no fees are due, however, should this be in error, please debit any applicable fees from Deposit Account No. 07-1185.

Respectfully submitted,

Date: _____

July 23, 2004



Benjamin Aaron Adler, Ph.D., J.D.

Counsel for Applicant

Registration No. 35,423

ADLER & ASSOCIATES
8011 Candle Lane
Houston, Texas 77071
(713) 270-5391
BADLER1@houston.rr.com